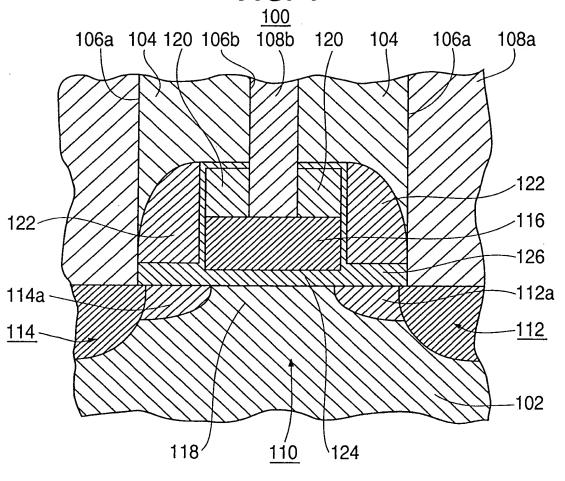




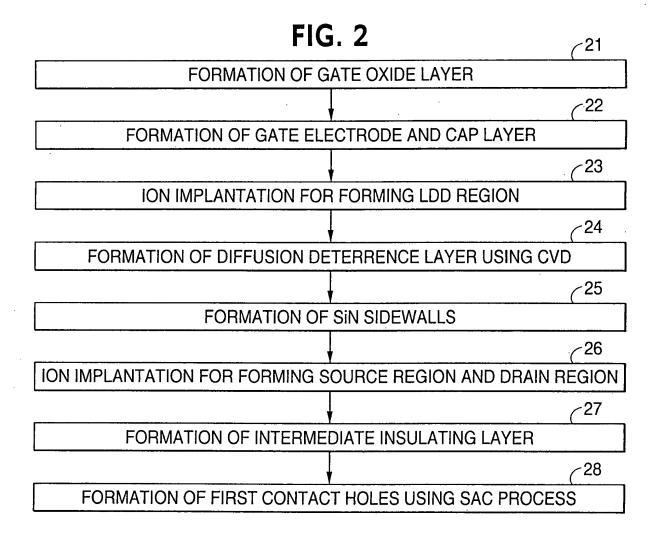
FIG. 1



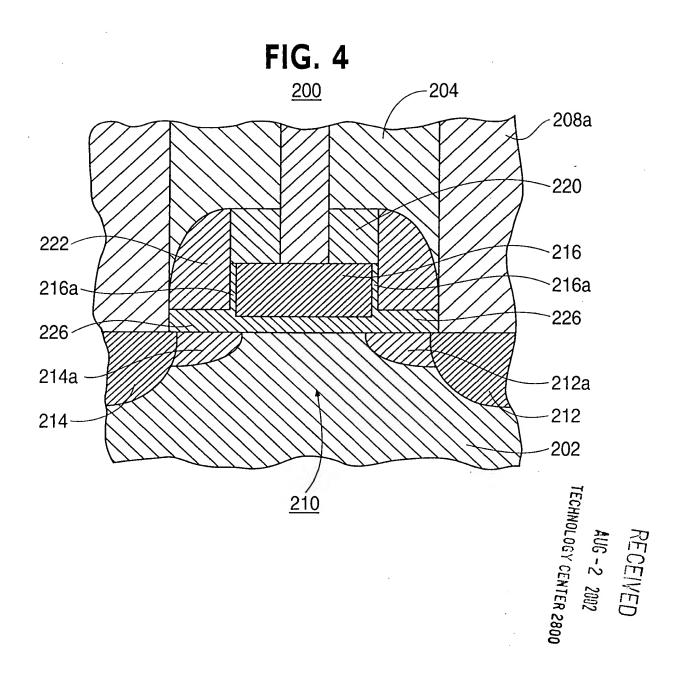




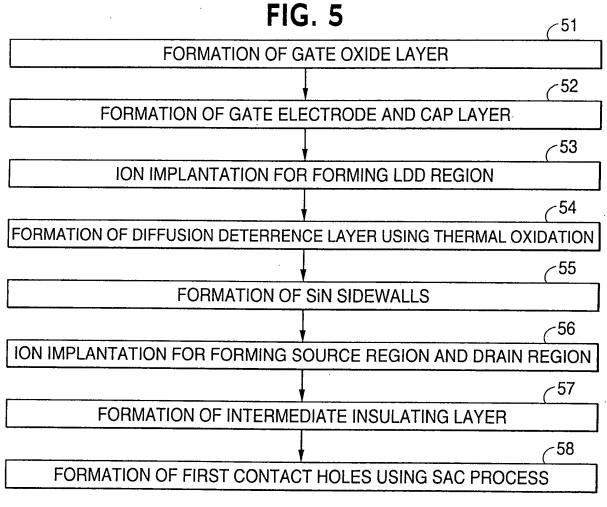




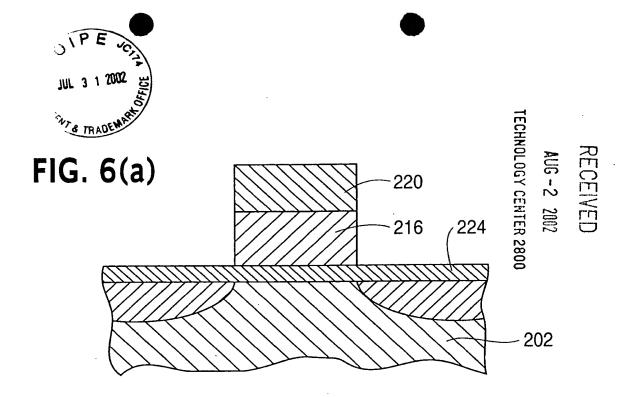


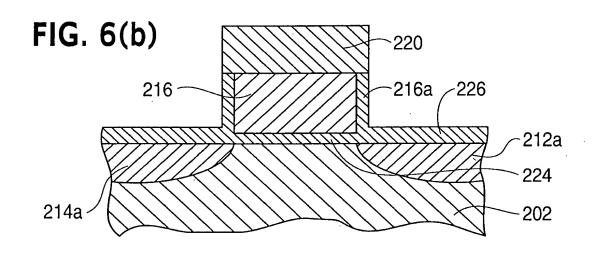


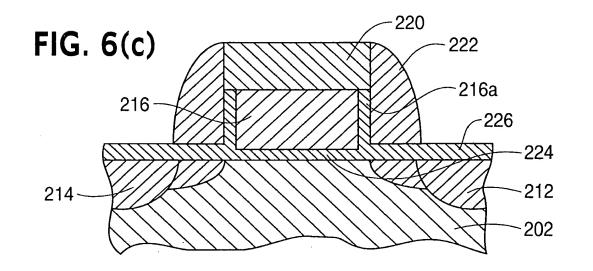




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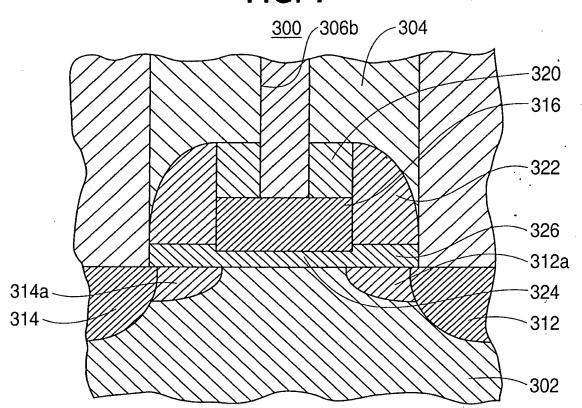




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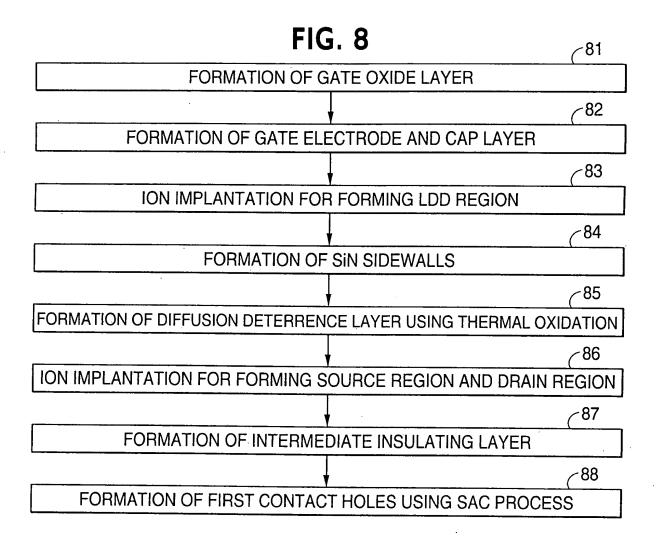
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FIG. 7





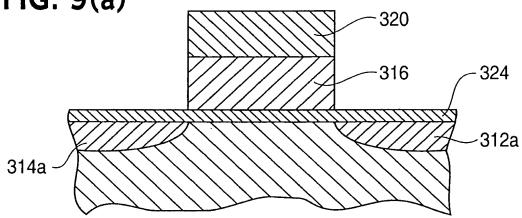


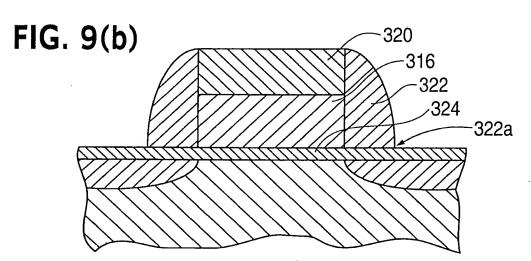


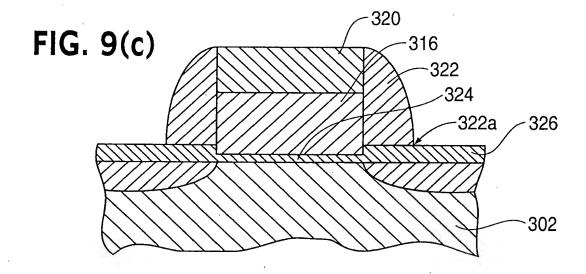


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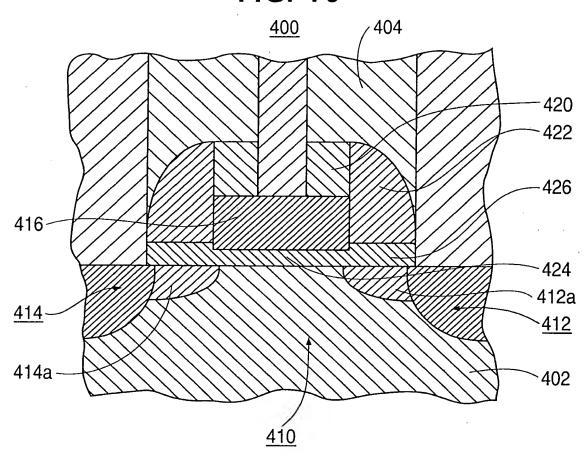






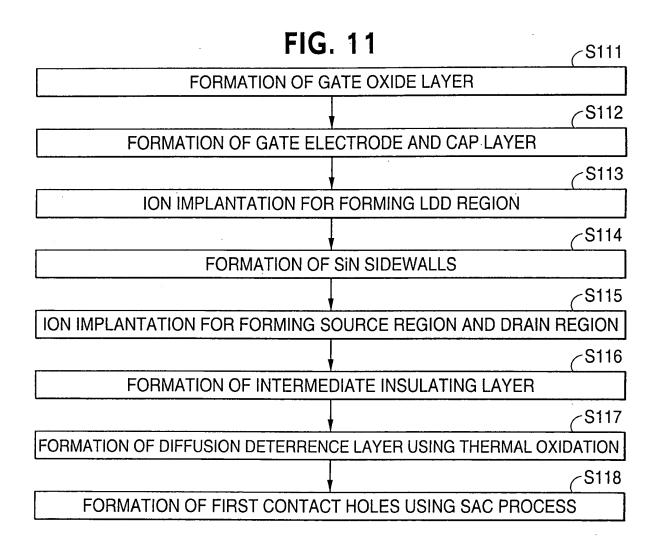
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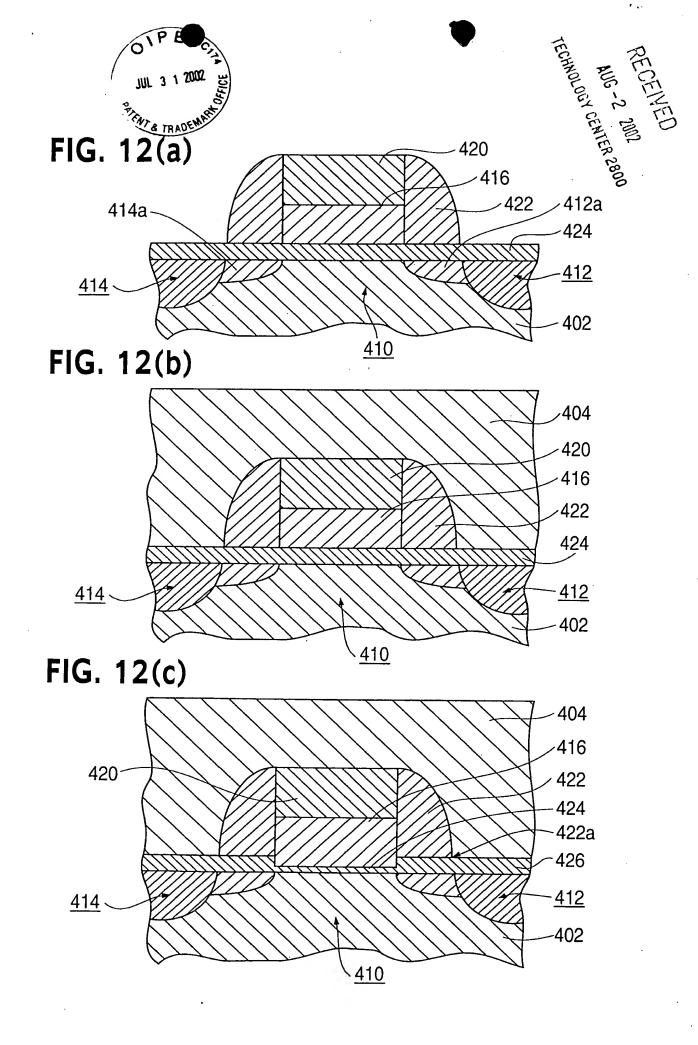
FIG. 10







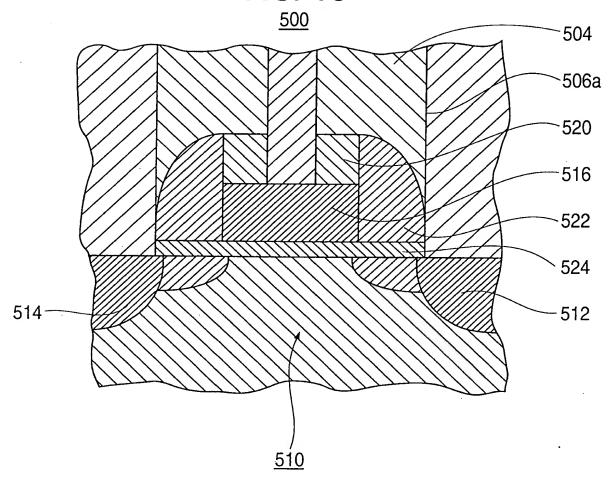






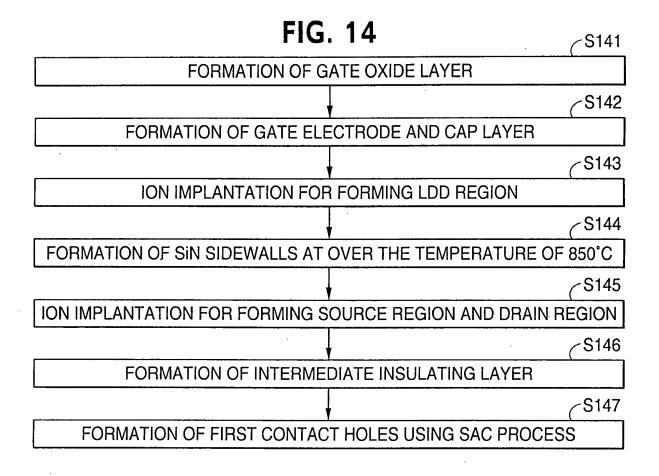




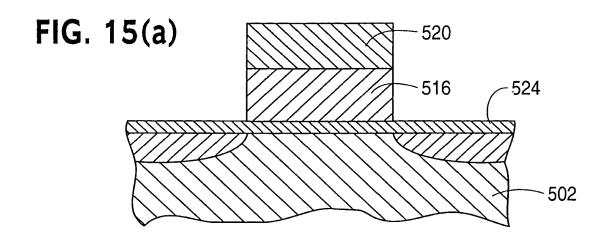


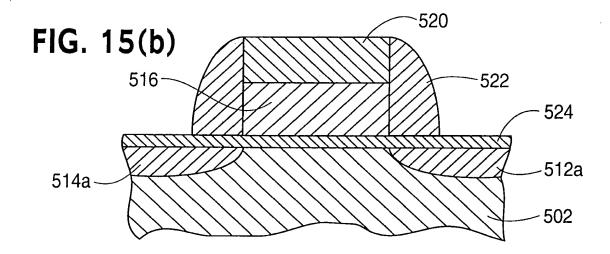
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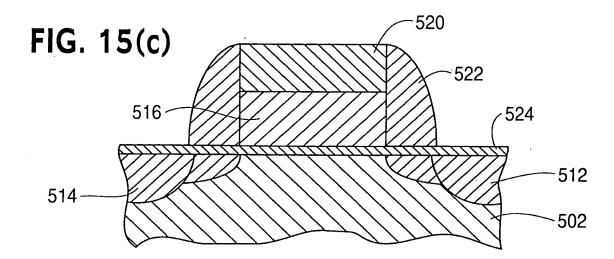
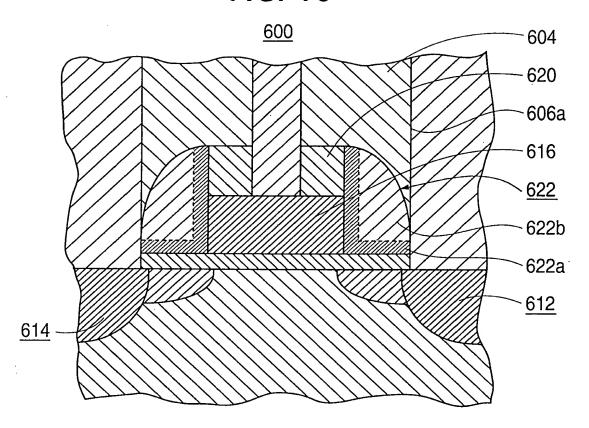




FIG. 16



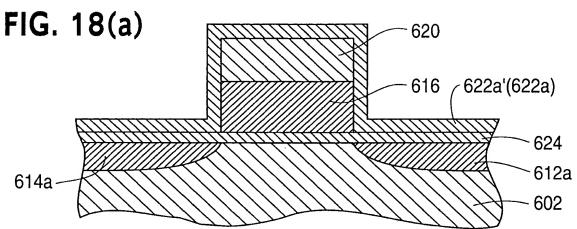
RECEIVED TOPS CENTER 2000

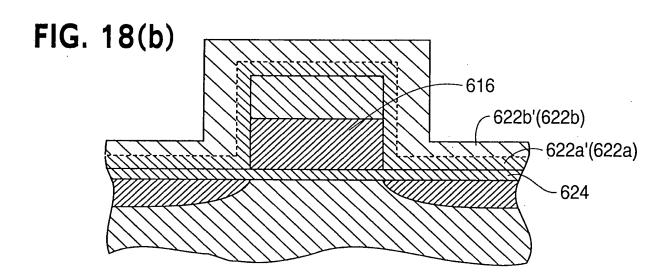


•	
FIG	. 17
FORMATION OF GATE OXIDE LAYER	
	S172
FORMATION OF GATE ELECTRODE AND CAP LAYER	
	S173
ION IMPLANTATION FOR FORMING LDD REGION	
	· · S174
FORMATION OF SIN SIDEWALLS AT OVER THE TEMPERATURE OF 850°C	
•	S175
FORMATION OF SIN SIDEWALLS AT THE TEMPERATURE OF ABOUT 780°C	
	S176
ION IMPLANTATION FOR FORMING SOURCE REGION AND DRAIN REGION	
	S177
FORMATION OF INTERMEDIATE INSULATING LAYER	
	S178
FORMATION OF FIRST CONTACT HOLES USING SAC PROCESS	



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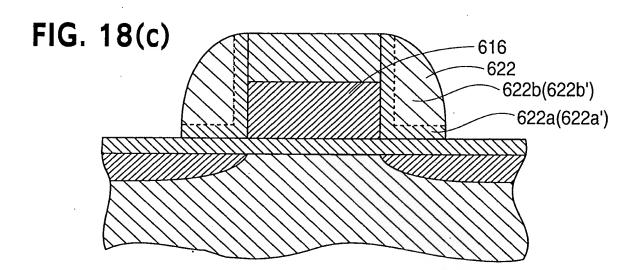
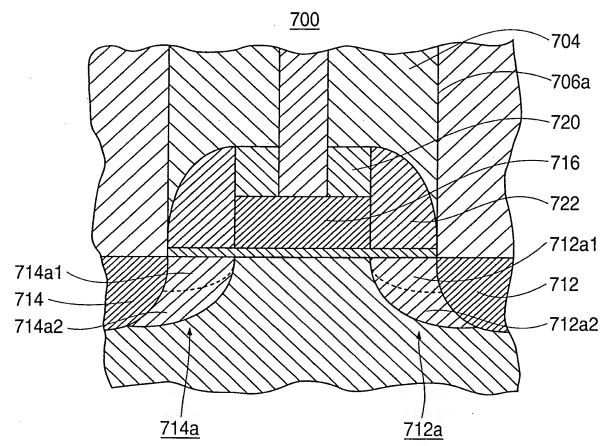


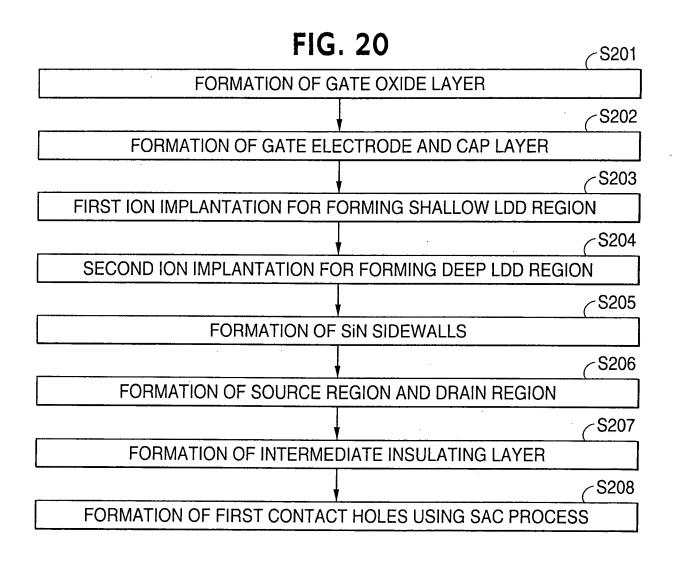


FIG. 19



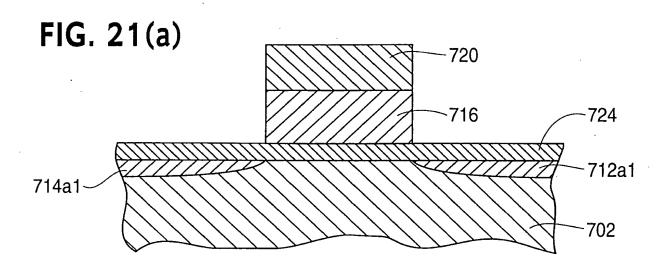


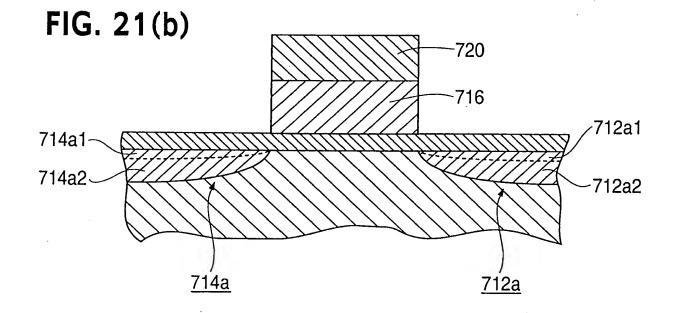
RECENTED PROPERTIES 2800 RUG-2 TOTAL PROPERTY OF THE PROPERTY



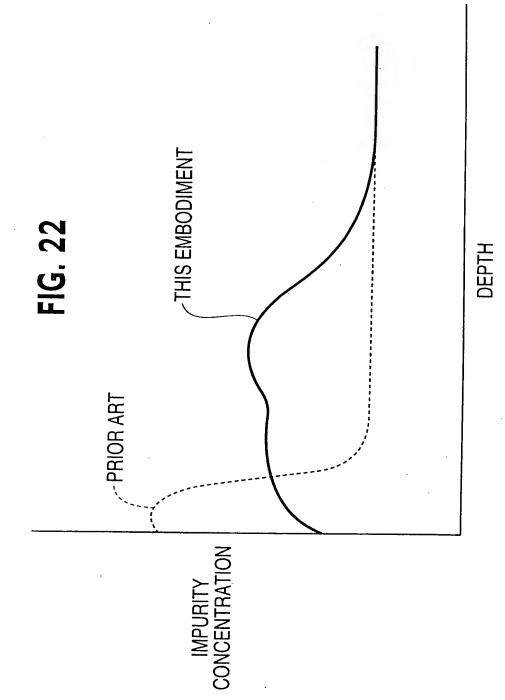














PRECENTED PRICE 2800 RUS - 2 PRICE CENTER 2800

FIG. 23 (PRIOR ART)

